

## ABSTRACT OF DISCLOSURE

A method including the steps of: consecutively  
5 depositing a first etch stop layer, a first compound  
semiconductor and a second compound semiconductor  
layer overlying a semiconductor substrate, the first etch  
stop layer, the first and second compound semiconductor  
layers having different compositions from one another,  
10 etching the first and second compound semiconductor  
layers until the etching stops at the first etch stop layer,  
and forming a semiconductor laser device including the  
first etch stop layer and the first and second compound  
semiconductor layers. The existence of the first  
15 compound semiconductor layer made of a material  
different from those of the second compound  
semiconductor layer and the etch stop layer enables the  
etching of the second compound semiconductor layer  
while controlling the etching depth thereof by using the  
20 etch stop layer.

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